

# Hong-Xia Liu

## List of Publications by Year in descending order

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140  
papers

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citations

430874

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h-index

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28  
g-index

140  
all docs

140  
docs citations

140  
times ranked

1137  
citing authors

| #  | ARTICLE  | IF  | CITATIONS |
|----|--|-----|-----------|
| 1  | Symmetric U-Shaped Gate Tunnel Field-Effect Transistor. IEEE Transactions on Electron Devices, 2017, 64, 1343-1349.  | 3.0 | 81        |
| 2  | Design of High Performance Si/SiGe Heterojunction Tunneling FETs with a T-Shaped Gate. Nanoscale Research Letters, 2017, 12, 198.  | 5.7 | 56        |
| 3  | Analog/RF Performance of T-Shape Gate Dual-Source Tunnel Field-Effect Transistor. Nanoscale Research Letters, 2018, 13, 321.   | 5.7 | 53        |
| 4  | TCAD Simulation of Single-Event-Transient Effects in L-Shaped Channel Tunneling Field-Effect Transistors. IEEE Transactions on Nuclear Science, 2018, 65, 2250-2259.                               | 2.0 | 42        |
| 5  | Tunable graphene-based hybrid plasmonic modulators for subwavelength confinement. Scientific Reports, 2017, 7, 5190.   | 3.3 | 40        |
| 6  | Physical properties and electrical characteristics of H <sub>2</sub> O-based and O <sub>3</sub> -based HfO <sub>2</sub> films deposited by ALD. Microelectronics Reliability, 2012, 52, 1043-1049. | 1.7 | 38        |
| 7  | A Multi-level Memristor Based on Al-Doped HfO <sub>2</sub> Thin Film. Nanoscale Research Letters, 2019, 14, 177.   | 5.7 | 38        |
| 8  | Reduced Miller Capacitance in U-Shaped Channel Tunneling FET by Introducing Heterogeneous Gate Dielectric. IEEE Electron Device Letters, 2017, 38, 403-406.  | 3.9 | 33        |
| 9  | Self-Compliance and High Performance Pt/HfO <sub>x</sub> /Ti RRAM Achieved through Annealing. Nanomaterials, 2020, 10, 457.  | 4.1 | 28        |
| 10 | Probing the Optical Properties of MoS <sub>2</sub> on SiO <sub>2</sub> /Si and Sapphire Substrates. Nanomaterials, 2019, 9, 740.   | 4.1 | 25        |
| 11 | Simulation and Performance Analysis of Dielectric Modulated Dual Source Trench Gate TFET Biosensor. Nanoscale Research Letters, 2021, 16, 34.  | 5.7 | 25        |
| 12 | A Novel Dopingless Fin-Shaped SiGe Channel TFET with Improved Performance. Nanoscale Research Letters, 2020, 15, 202.  | 5.7 | 25        |
| 13 | Analog/RF performance of L- and U-shaped channel tunneling field-effect transistors and their application as digital inverters. Japanese Journal of Applied Physics, 2017, 56, 064102.             | 1.5 | 23        |
| 14 | Defect Detection of IC Wafer Based on Spectral Subtraction. IEEE Transactions on Semiconductor Manufacturing, 2010, 23, 141-147.   | 1.7 | 22        |
| 15 | Optical Transport Properties of Graphene Surface Plasmon Polaritons in Mid-Infrared Band. Crystals, 2019, 9, 354.  | 2.2 | 22        |
| 16 | Volatile and Nonvolatile Memory Operations Implemented in a Pt/HfO <sub>2</sub> /Ti Memristor. IEEE Transactions on Electron Devices, 2021, 68, 1622-1626.   | 3.0 | 22        |
| 17 | Hybrid Tube-Triangle Plasmonic Waveguide for Ultradeep Subwavelength Confinement. Journal of Lightwave Technology, 2017, 35, 2259-2265.  | 4.6 | 21        |
| 18 | Magnetism investigation of GaN monolayer doped with group VIII B transition metals. Journal of Materials Science, 2018, 53, 15986-15994.   | 3.7 | 20        |

| #  | ARTICLE  | IF  | CITATIONS |
|----|--|-----|-----------|
| 19 | Structural Properties Characterized by the Film Thickness and Annealing Temperature for La <sub>2</sub> O <sub>3</sub> Films Grown by Atomic Layer Deposition. Nanoscale Research Letters, 2017, 12, 233.  | 5.7 | 19        |
| 20 | Multi-Level Switching of Al-Doped HfO <sub>2</sub> RRAM with a Single Voltage Amplitude Set Pulse. Electronics (Switzerland), 2021, 10, 731.   | 3.1 | 19        |
| 21 | Improvement of Electrical Performance in Heterostructure Junctionless TFET Based on Dual Material Gate. Applied Sciences (Switzerland), 2020, 10, 126.   | 2.5 | 18        |
| 22 | Defect detection of IC wafer based on two-dimension wavelet transform. Microelectronics Journal, 2010, 41, 171-177.  | 2.0 | 17        |
| 23 | The influence of process parameters and pulse ratio of precursors on the characteristics of La <sub>1-x</sub> Al <sub>x</sub> O <sub>3</sub> films deposited by atomic layer deposition. Nanoscale Research Letters, 2015, 10, 180.                              | 5.7 | 17        |
| 24 | Theoretical research of diluted magnetic semiconductors: GaN monolayer doped with transition metal atoms. Superlattices and Microstructures, 2018, 120, 382-388.   | 3.1 | 16        |
| 25 | Sensitivity Analysis of Biosensors Based on a Dielectric-Modulated L-Shaped Gate Field-Effect Transistor. Micromachines, 2021, 12, 19.   | 2.9 | 16        |
| 26 | Silicon diffusion control in atomic-layer-deposited Al <sub>2</sub> O <sub>3</sub> /La <sub>2</sub> O <sub>3</sub> /Al <sub>2</sub> O <sub>3</sub> gate stacks using an Al <sub>2</sub> O <sub>3</sub> barrier layer. Nanoscale Research Letters, 2015, 10, 141. | 5.7 | 15        |
| 27 | Impacts of Cu-Doping on the Performance of La-Based RRAM Devices. Nanoscale Research Letters, 2019, 14, 224.   | 5.7 | 15        |
| 28 | Analog/RF performance of four different Tunneling FETs with the recessed channels. Superlattices and Microstructures, 2016, 100, 1238-1248.  | 3.1 | 14        |
| 29 | Modulation speed limits of a graphene-based modulator. Optical and Quantum Electronics, 2018, 50, 1.   | 3.3 | 14        |
| 30 | Design and Investigation of the Junction-Less TFET with Ge/Si <sub>0.3</sub> Ge <sub>0.7</sub> /Si Heterojunction and Heterogeneous Gate Dielectric. Electronics (Switzerland), 2019, 8, 476.  | 3.1 | 14        |
| 31 | Negative differential resistance in single-walled SiC nanotubes. Science Bulletin, 2008, 53, 3770-3772.  | 1.7 | 13        |
| 32 | Monte Carlo calculation of electron diffusion coefficient in wurtzite indium nitride. Applied Physics Letters, 2012, 100, 142105.  | 3.3 | 13        |
| 33 | Electrical performance of InAs/GaAs <sub>0.1</sub> Sb <sub>0.9</sub> heterostructure junctionless TFET with dual-material gate and Gaussian-doped source. Semiconductor Science and Technology, 2020, 35, 095004.  | 2.0 | 13        |
| 34 | Two ESD Detection Circuits for 3× VDD-Tolerant I/O Buffer in Low-Voltage CMOS Processes With Low Leakage Currents. IEEE Transactions on Device and Materials Reliability, 2013, 13, 319-321.   | 2.0 | 12        |
| 35 | Design and investigation of a dual source and U-shaped gate TFET with n buffer and SiGe pocket. AIP Advances, 2020, 10, .  | 1.3 | 12        |
| 36 | An analytical model of low field and high field electron mobility in wurtzite indium nitride. Journal of Materials Science: Materials in Electronics, 2016, 27, 11353-11357.   | 2.2 | 11        |

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|----|--|-----|-----------|
| 37 | A 130 GHz Electro-Optic Ring Modulator with Double-Layer Graphene. Crystals, 2017, 7, 65.  | 2.2 | 11        |
| 38 | Graphene-Hexagonal Boron Nitride Heterostructure as a Tunable Phononâ€“Plasmon Coupling System. Crystals, 2017, 7, 49.   | 2.2 | 11        |
| 39 | Electrical Properties and Interfacial Issues of HfO <sub>2</sub> /Ge MIS Capacitors Characterized by the Thickness of La <sub>2</sub> O <sub>3</sub> Interlayer. Nanomaterials, 2019, 9, 697.                              | 4.1 | 11        |
| 40 | Fabrication and Characterization of MoS <sub>2</sub> /h-BN and WS <sub>2</sub> /h-BN Heterostructures. Micromachines, 2020, 11, 1114.  | 2.9 | 11        |
| 41 | TCAD simulation of a double L-shaped gate tunnel fieldâ€“effect transistor with a covered sourceâ€“channel. Micro and Nano Letters, 2020, 15, 272-276.   | 1.3 | 11        |
| 42 | Identification of optimal ALD process conditions of Nd <sub>2</sub> O <sub>3</sub> on Si by spectroscopic ellipsometry. Applied Physics A: Materials Science and Processing, 2014, 114, 545-550.                           | 2.3 | 10        |
| 43 | A high performance Ge/Si 0.5 Ge 0.5 /Si heterojunction dual sources tunneling transistor with a U-shaped channel. Superlattices and Microstructures, 2017, 106, 8-19.  | 3.1 | 10        |
| 44 | Probing the Field-Effect Transistor with Monolayer MoS <sub>2</sub> Prepared by APCVD. Nanomaterials, 2019, 9, 1209.   | 4.1 | 10        |
| 45 | A Horizontal-Gate Monolayer MoS <sub>2</sub> Transistor Based on Image Force Barrier Reduction. Nanomaterials, 2019, 9, 1245.  | 4.1 | 10        |
| 46 | Design and Investigation of the High Performance Doping-Less TFET with Ge/Si <sub>0.6</sub> Ge <sub>0.4</sub> /Si Heterojunction. Micromachines, 2019, 10, 424.  | 2.9 | 10        |
| 47 | Design and investigation of dopingless dual-gate tunneling transistor based on line tunneling. AIP Advances, 2019, 9, .  | 1.3 | 10        |
| 48 | A New Electro-Optical Switch Modulator Based on the Surface Plasmon Polaritons of Graphene in Mid-Infrared Band. Sensors, 2019, 19, 89.  | 3.8 | 10        |
| 49 | Performance investigations of novel dual-material gate (DMG) MOSFET with dielectric pockets (DP). Science in China Series D: Earth Sciences, 2009, 52, 2400-2405.  | 0.9 | 9         |
| 50 | Influence of different oxidants on the band alignment of HfO <sub>2</sub> films deposited by atomic layer deposition. Chinese Physics B, 2012, 21, 087702.   | 1.4 | 9         |
| 51 | A novel Ge based overlapping gate dopingless tunnel FET with high performance. Japanese Journal of Applied Physics, 2019, 58, 100902.  | 1.5 | 9         |
| 52 | A Doping-Less Tunnel Field-Effect Transistor with Si <sub>0.6</sub> Ge <sub>0.4</sub> Heterojunction for the Improvement of the Onâ€“Off Current Ratio and Analog/RF Performance. Electronics (Switzerland), 2019, 8, 574. | 3.1 | 9         |
| 53 | Probing the Growth Improvement of Large-Size High Quality Monolayer MoS <sub>2</sub> by APCVD. Nanomaterials, 2019, 9, 433.  | 4.1 | 9         |
| 54 | First-Principles Study on the Effect of Strain on Single-Layer Molybdenum Disulfide. Nanomaterials, 2021, 11, 3127.  | 4.1 | 9         |

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|----|--|-----|-----------|
| 55 | Optical characteristics of H <sub>2</sub> O-based and O <sub>3</sub> -based HfO <sub>2</sub> films deposited by ALD using spectroscopy ellipsometry. Applied Physics A: Materials Science and Processing, 2015, 119, 957-963.  | 2.3 | 8         |
| 56 | Impacts of Annealing Conditions on the Flat Band Voltage of Alternate La <sub>2</sub> O <sub>3</sub> /Al <sub>2</sub> O <sub>3</sub> Multilayer Stack Structures. Nanoscale Research Letters, 2016, 11, 394.   | 5.7 | 8         |
| 57 | Design and Investigation of a Dual Material Gate Arsenic Alloy Heterostructure Junctionless TFET with a Lightly Doped Source. Applied Sciences (Switzerland), 2019, 9, 4104.   | 2.5 | 8         |
| 58 | Graphene Electro-Optical Switch Modulator by Adjusting Propagation Length Based on Hybrid Plasmonic Waveguide in Infrared Band. Sensors, 2020, 20, 2864.   | 3.8 | 8         |
| 59 | Electrical Phase Control Based on Graphene Surface Plasmon Polaritons in Mid-infrared. Nanomaterials, 2020, 10, 576.   | 4.1 | 8         |
| 60 | Research on the Preparation and Spectral Characteristics of Graphene/TMDs Hetero-structures. Nanoscale Research Letters, 2020, 15, 219.  | 5.7 | 8         |
| 61 | Modeling and Simulation of Hafnium Oxide RRAM Based on Oxygen Vacancy Conduction. Crystals, 2021, 11, 1462.  | 2.2 | 8         |
| 62 | Influences of different oxidants on the characteristics of HfAlO <sub>x</sub> films deposited by atomic layer deposition. Chinese Physics B, 2013, 22, 027702.   | 1.4 | 7         |
| 63 | The optical properties of GaN (001) surface modified by intrinsic defects from density functional theory calculation. Optik, 2018, 154, 378-382.   | 2.9 | 7         |
| 64 | A Long Propagation Distance Hybrid Triangular Prism Waveguide for Ultradeep Subwavelength Confinement. IEEE Sensors Journal, 2019, 19, 11159-11166.  | 4.7 | 7         |
| 65 | Improved resistive switching characteristics of atomic layer deposited Al <sub>2</sub> O <sub>3</sub> /La <sub>2</sub> O <sub>3</sub> /Al <sub>2</sub> O <sub>3</sub> multi-stacked films with Al <sup>+</sup> implantation. Journal of Materials Science: Materials in Electronics, 2019, 30, 12577-12583.                        | 2.2 | 7         |
| 66 | Wide-Range Tunable Narrow Band-Stop Filter Based on Bilayer Graphene in the Mid-Infrared Region. IEEE Photonics Journal, 2020, 12, 1-9.  | 2.0 | 7         |
| 67 | The Large-Scale Preparation and Optical Properties of MoS <sub>2</sub> /WS <sub>2</sub> Vertical Hetero-Junction. Molecules, 2020, 25, 1857.   | 3.8 | 7         |
| 68 | Frequency dispersion effect and parameters extraction method for novel HfO <sub>2</sub> as gate dielectric. Science China Information Sciences, 2010, 53, 878-884.   | 4.3 | 6         |
| 69 | Influences of rapid thermal annealing on the characteristics of Al <sub>2</sub> O <sub>3</sub> /La <sub>2</sub> O <sub>3</sub> /Si and La <sub>2</sub> O <sub>3</sub> /Al <sub>2</sub> O <sub>3</sub> /Si films deposited by atomic layer deposition. Journal of Materials Science: Materials in Electronics, 2016, 27, 8550-8558. | 2.2 | 6         |
| 70 | The Study of Electrical Properties for Multilayer La <sub>2</sub> O <sub>3</sub> /Al <sub>2</sub> O <sub>3</sub> Dielectric Stacks and LaAlO <sub>3</sub> Dielectric Film Deposited by ALD. Nanoscale Research Letters, 2017, 12, 230.   | 5.7 | 6         |
| 71 | Effects of Annealing Ambient on the Characteristics of LaAlO <sub>3</sub> Films Grown by Atomic Layer Deposition. Nanoscale Research Letters, 2017, 12, 108.   | 5.7 | 6         |
| 72 | Research on the Factors Affecting the Growth of Large-Size Monolayer MoS <sub>2</sub> by APCVD. Materials, 2018, 11, 2562.   | 2.9 | 6         |

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|----|--|-----|-----------|
| 73 | Study of a Gate-Engineered Vertical TFET with GaSb/GaAs <sub>0.5</sub> Sb <sub>0.5</sub> Heterojunction. Materials, 2021, 14, 1426.  | 2.9 | 6         |
| 74 | Impacts of LaOx Doping on the Performance of ITO/Al <sub>2</sub> O <sub>3</sub> /ITO Transparent RRAM Devices. Electronics (Switzerland), 2021, 10, 272.   | 3.1 | 6         |
| 75 | A high performance trench gate tunneling field effect transistor based on quasi-broken gap energy band alignment heterojunction. Nanotechnology, 2022, 33, 225205.   | 2.6 | 6         |
| 76 | Monte Carlo transport simulation of velocity undershoot in zinc blende and wurtzite InN. Physica Status Solidi (B): Basic Research, 2012, 249, 1761-1764.  | 1.5 | 5         |
| 77 | Improvement of the Anneal-Induced Valence Band Offset Variation by the Hybrid Deposition of $\text{HfO}_2$ on Si. IEEE Transactions on Electron Devices, 2013, 60, 1536-1539.  | 3.0 | 5         |
| 78 | Band alignments of O <sub>3</sub> -based and H <sub>2</sub> O-based amorphous LaAlO <sub>3</sub> films on silicon by atomic layer deposition. Journal of Materials Science: Materials in Electronics, 2017, 28, 803-807. | 2.2 | 5         |
| 79 | The Programming Optimization of Capacitorless 1T DRAM Based on the Dual-Gate TFET. Nanoscale Research Letters, 2017, 12, 524.  | 5.7 | 5         |
| 80 | Electron Momentum and Energy Relaxation Times in Wurtzite GaN, InN and AlN: A Monte Carlo Study. Journal of Electronic Materials, 2018, 47, 1560-1568.   | 2.2 | 5         |
| 81 | Improvements on the Interfacial Properties of High-k/Ge MIS Structures by Inserting a La <sub>2</sub> O <sub>3</sub> Passivation Layer. Materials, 2018, 11, 2333.   | 2.9 | 5         |
| 82 | Effect of the High-Temperature Off-State Stresses on the Degradation of AlGaIn/GaN HEMTs. Electronics (Switzerland), 2019, 8, 1339.  | 3.1 | 5         |
| 83 | Study on Single Event Effect Simulation in T-Shaped Gate Tunneling Field-Effect Transistors. Micromachines, 2021, 12, 609.   | 2.9 | 5         |
| 84 | Investigation of charge trapping mechanism in MoS <sub>2</sub> field effect transistor by incorporating Al into host La <sub>2</sub> O <sub>3</sub> as gate dielectric. Nanotechnology, 2021, 32, 305201.                | 2.6 | 5         |
| 85 | Low-Power OR Logic Ferroelectric In-Situ Transistor Based on a CuInP <sub>2</sub> S <sub>6</sub> /MoS <sub>2</sub> Van Der Waals Heterojunction. Nanomaterials, 2021, 11, 1971.  | 4.1 | 5         |
| 86 | Preparation and Research of Monolayer WS <sub>2</sub> FETs Encapsulated by h-BN Material. Micromachines, 2021, 12, 1006.   | 2.9 | 5         |
| 87 | Research on Total Ionizing Dose Effect and Reinforcement of SOI-TFET. Micromachines, 2021, 12, 1232.   | 2.9 | 5         |
| 88 | Polarization Gradient Effect of Negative Capacitance LTFET. Micromachines, 2022, 13, 344.  | 2.9 | 5         |
| 89 | Polarization properties in grating-gated AlN/GaN HEMTs at mid-infrared frequencies. Optics Express, 2022, 30, 14748.   | 3.4 | 5         |
| 90 | Hybrid Nanowire-Rectangular Plasmonic Waveguide for Subwavelength Confinement at 1550 Nm. Micromachines, 2022, 13, 1009.   | 2.9 | 5         |

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|-----|--|-----|-----------|
| 91  | Electrical properties and interfacial issues of high- $\kappa$ /Si MIS capacitors characterized by the thickness of Al <sub>2</sub> O <sub>3</sub> interlayer. AIP Advances, 2016, 6, .                              | 1.3 | 4         |
| 92  | Effects of Rapid Thermal Annealing and Different Oxidants on the Properties of La <sub>x</sub> Al <sub>y</sub> O Nanolaminate Films Deposited by Atomic Layer Deposition. Nanoscale Research Letters, 2017, 12, 218. | 5.7 | 4         |
| 93  | Analog/RF performance of two tunnel FETs with symmetric structures. Superlattices and Microstructures, 2017, 111, 568-573.   | 3.1 | 4         |
| 94  | The Optimization of Spacer Engineering for Capacitor-Less DRAM Based on the Dual-Gate Tunneling Transistor. Nanoscale Research Letters, 2018, 13, 73.  | 5.7 | 4         |
| 95  | Impact of remote oxygen scavenging on the interfacial characteristics of atomic layer deposited LaAlO <sub>3</sub> . Materials Science in Semiconductor Processing, 2019, 90, 50-53.                                 | 4.0 | 4         |
| 96  | Comprehensive Performance Quasi-Non-Volatile Memory Compatible with Large-Scale Preparation by Chemical Vapor Deposition. Nanomaterials, 2020, 10, 1471.   | 4.1 | 4         |
| 97  | TCAD Simulation of the Doping-Less TFET with Ge/SiGe/Si Hetero-Junction and Hetero-Gate Dielectric for the Enhancement of Device Performance. Coatings, 2020, 10, 278.   | 2.6 | 4         |
| 98  | Low-power design and application based on CSD optimization for a fixed coefficient multiplier. Science China Information Sciences, 2011, 54, 2443-2453.  | 4.3 | 3         |
| 99  | Molecular dynamics simulation of latent track formation in bilayer graphene. IEICE Electronics Express, 2015, 12, 20150771-20150771.   | 0.8 | 3         |
| 100 | Research on the origin of negative effect in uniform doping GaN-based Gunn diode under THz frequency. Applied Physics A: Materials Science and Processing, 2016, 122, 1.   | 2.3 | 3         |
| 101 | The Effect of Ion Irradiation Density on the Defect of Graphene: A Molecular Dynamics Study. Crystals, 2020, 10, 158.  | 2.2 | 3         |
| 102 | Adjusting transmissivity based on graphene-h-BN-graphene heterostructure as a tunable phonon-plasmon coupling system in mid-infrared band. Journal of Materials Science, 2021, 56, 3210-3219.                        | 3.7 | 3         |
| 103 | A subwavelength high modulation depth optical modulator based on bilayer graphene. Optical Materials, 2021, 117, 111139.   | 3.6 | 3         |
| 104 | A waveguide-integrated graphene-based subwavelength electro-optic switch at 1550 nm. Optics Communications, 2021, 495, 127121.   | 2.1 | 3         |
| 105 | Interface optimization of La-based gate dielectric for molybdenum disulfide field-effect transistors. Applied Surface Science, 2022, 581, 152248.  | 6.1 | 3         |
| 106 | The Image Identification Application with HfO <sub>2</sub> -Based Replaceable 1T1R Neural Networks. Nanomaterials, 2022, 12, 1075.   | 4.1 | 3         |
| 107 | Electrical and Thermal Characteristics of AlGaIn/GaN HEMT Devices with Dual Metal Gate Structure: A Theoretical Investigation. Materials, 2022, 15, 3818.  | 2.9 | 3         |
| 108 | Interaction of NBTI with Hot Carriers in PMOSFET's for Advanced CMOS Technologies. , 2006, , .   |     | 2         |

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|-----|--|-----|-----------|
| 109 | An analytical model of anisotropic low-field electron mobility in wurtzite indium nitride. Applied Physics A: Materials Science and Processing, 2014, 114, 1113-1117.  | 2.3 | 2         |
| 110 | Effects of total dose irradiation on the threshold voltage of H-gate SOI NMOS devices. Nuclear Science and Techniques/Hewuli, 2016, 27, 1.   | 3.4 | 2         |
| 111 | Multiscale simulations of swift heavy ion irradiation effect on bilayer graphene. IEICE Electronics Express, 2016, 13, 20151040-20151040.  | 0.8 | 2         |
| 112 | Band alignments of $\text{La}_x\text{Al}_y\text{O}$ films on Si substrates grown by atomic layer deposition with different La/Al atomic ratios. Journal of Materials Science: Materials in Electronics, 2017, 28, 4702-4705. | 2.2 | 2         |
| 113 | Improvement of the high- $\text{I}_\text{p}$ /Ge interface thermal stability using an in-situ ozone treatment characterized by conductive atomic force microscopy. Chinese Physics B, 2017, 26, 087701.                      | 1.4 | 2         |
| 114 | The influence of La/Al atomic ratio on the dielectric constant and band-gap of stack-gate $\text{LaAlO}_3/\text{SiO}_2$ structure. Journal of Materials Science: Materials in Electronics, 2017, 28, 2004-2008.              | 2.2 | 2         |
| 115 | The Influence of Copper Substrates on Irradiation Effects of Graphene: A Molecular Dynamics Study. Materials, 2019, 12, 319.   | 2.9 | 2         |
| 116 | Synthesis and Spectral Characteristics Investigation of the 2D-2D vdWs Heterostructure Materials. International Journal of Molecular Sciences, 2021, 22, 1246.   | 4.1 | 2         |
| 117 | Construction and electrical performance improvement of $\text{MoS}_2$ FET with graphene/metal contact. Optical Materials Express, 2021, 11, 3099.  | 3.0 | 2         |
| 118 | Atomic Layer Deposition of Ultrathin $\text{La}_2\text{O}_3/\text{Al}_2\text{O}_3$ Nanolaminates on $\text{MoS}_2$ with Ultraviolet Ozone Treatment. Materials, 2022, 15, 1794.  | 2.9 | 2         |
| 119 | A new method of thin gate $\text{SiO}_2$ reliability characterization. Surface and Interface Analysis, 2002, 34, 437-440.  | 1.8 | 1         |
| 120 | Anisotropic longitudinal electron diffusion coefficient in wurtzite gallium nitride. Applied Physics A: Materials Science and Processing, 2013, 112, 933-938.  | 2.3 | 1         |
| 121 | Anisotropic low-field electron diffusion coefficient and mobility in wurtzite indium nitride. Physica Status Solidi (B): Basic Research, 2014, 251, 168-171.   | 1.5 | 1         |
| 122 | Total ionizing dose effect of gamma rays on H-gate PDSOI MOS devices at different dose rates. Nuclear Science and Techniques/Hewuli, 2017, 28, 1.  | 3.4 | 1         |
| 123 | Impacts of the Oxygen Precursor on the Interfacial Properties of $\text{La}_x\text{Al}_y\text{O}$ Films Grown by Atomic Layer Deposition on Ge. Materials, 2017, 10, 856.  | 2.9 | 1         |
| 124 | Research of Heterogeneous Acceleration Optimization of Convolutional Neural Network Algorithm for Unmanned Vehicle Based on FPGA. , 2019, , .  |     | 1         |
| 125 | Filtering Characteristics of Phonon Polaritons Waves Based on Dielectric-h-BN-Dielectric Structure in Mid-Infrared Band. Nanomaterials, 2020, 10, 878.   | 4.1 | 1         |
| 126 | Robust and Latch-Up-Immune LVTSCR Device with an Embedded PMOSFET for ESD Protection in a 28-nm CMOS Process. Nanoscale Research Letters, 2020, 15, 212.   | 5.7 | 1         |



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|-----|---|-----|-----------|
| 127 | DC and pulsed DC stress evolution in copper interconnects. , 2006, , .  |     | 0         |
| 128 | Numerical Analysis of Barrier Layer Effect on Copper Electromigration. , 2006, , .  |     | 0         |
| 129 | Characteristics analysis and optimization design of a new ESD power clamp circuit. Microelectronics Reliability, 2010, 50, 1087-1093.   | 1.7 | 0         |
| 130 | Investigation of electrical characteristics of $\text{NdAlO}_3/\text{SiO}_2/\text{stack gate}$ . , 2010, , .  |     | 0         |
| 131 | Modeling of enhancement factor of hole mobility for strained silicon under low stress intensity. Microelectronics Reliability, 2011, 51, 909-913.                                 | 1.7 | 0         |
| 132 | A modified ESD clamp circuit for 90-nm CMOS process. , 2012, , .  |     | 0         |
| 133 | Off-state leakage current of nano-scaled MOSFETs with high-k gate dielectric. , 2012, , .   |     | 0         |
| 134 | A novel ESD power supply clamp circuit with double pull-down paths. Science China Information Sciences, 2013, 56, 1-8.  | 4.3 | 0         |
| 135 | Enhanced Electrical Properties of Atomic Layer Deposited $\text{LaAlO}_3$ Thin Films with Stress Relieved Preoxide Pretreatment. Materials, 2018, 11, 1601.                       | 2.9 | 0         |
| 136 | Impact of $\text{Al}^+$ implantation on the Switching Characteristics of $\text{Al}_2\text{O}_3/\text{La}_2\text{O}_3/\text{Al}_2\text{O}_3$ multilayer RRAM devices. , 2019, , . |     | 0         |
| 137 | Enhanced Interfacial Characteristics of Atomic Layer Deposited $\text{LaAlO}_3$ Thin Films. , 2019, , .   |     | 0         |
| 138 | Simulation of Displacement Damage in Nanoscale MOSFET Caused by Galactic Cosmic Rays. Journal of Computational and Theoretical Nanoscience, 2016, 13, 5242-5246.                  | 0.4 | 0         |
| 139 | Research on Transparent Resistive Random Memory Based on Lanthanum-based High-k Medium. , 2021, , .   |     | 0         |
| 140 | Investigation of Negative Bias Temperature Instability Effect in Nano PDSOI PMOSFET. Micromachines, 2022, 13, 808.  | 2.9 | 0         |